











INA138-Q1, INA168-Q1

ZHCSFO0J - SEPTEMBER 2003 - REVISED AUGUST 2018

INA1x8-Q1 汽车级高侧电流输出分流监测计

特性

- 符合汽车类应用的 要求
- 具有符合 AEC-Q100 标准的下列特性:
 - 器件温度 1 级: -40°C 至 125°C 的环境工作温 度范围
 - 器件 HBM ESD 分类等级 2
 - 器件 CDM ESD 分类等级 C6
- 完备的单极高侧电流测量电路
- 宽电源电压和共模电压范围:
 - INA138-Q1: 2.7V 至 36V
 - INA168-Q1: 2.7V 至 60V
- 独立电源和输入共模电压
- 单电阻增益设定
- 低静态电流: 25µA (典型值)
- 宽温度范围: -40°C 至 +125°C
- 封装: 薄型小外形尺寸 (TSSOP)-8、小外形尺寸晶 体管 (SOT) 23-5 (INA168-Q1)

2 应用

- 电动助力转向 (EPS) 系统
- 车身控制模块
- 刹车系统
- 电子稳定性控制 (ESC) 系统

3 说明

INA138-Q1 和 INA168-Q1 (INA1x8-Q1) 器件是高侧单 向电流感应放大器。凭借宽输入共模电压范围、低静态 电流以及 TSSOP 和 SOT-23 封装,此类器件广泛适 用于 各种应用。

输入共模电压与电源电压互不影响, INA138-Q1 与 INA168-Q1 的电压范围分别为 2.7V 至 36V 以及 2.7V 至 60V。静态电流仅为 25μA, 允许在误差最低的情况 下将电源与电流测量分流器的任意一侧相连。

该器件可将一个差分输入电压转换为电流输出。此电流 使用外部负载电阻转换回电压, 该电阻可设置的增益范 围为 1 至 100 以上。尽管该电路专为分流测量而设 计,但同时也非常适用于创造性应用中的测量和电平 转换。

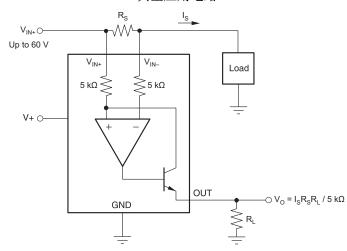
两类器件均采用 TSSOP-8 封装。INA168-Q1 还可采 用 SOT-23-5 封装。两类器件的额定工作温度范围均为 -40°C 至 +125°C。

器件信息⁽¹⁾

,,, =							
器件型号	封装	封装尺寸 (标称值)					
INA138-Q1	TCCOD (0)	4 40					
INA168-Q1	TSSOP (8)	4.40mm x 3.00mm					
INA168-Q1	SOT-23 (5)	2.90mm × 1.60mm					

(1) 要了解所有可用封装,请参见数据表末尾的封装选项附录。

典型应用电路



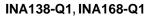


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4 修订历史记录

注: 之前版本的页码可能与当前版本有所不同。

CI	nanges from Revision I (January 2018) to Revision J	ge
•	Added "V _{SENSE} =" to differential analog input voltage label in <i>Absolute Maximum Ratings</i> table	. 5
•	Changed maximum differential analog input voltage from 2 V to 40 V in Absolute Maximum Ratings table	. 5
•	Added new note 2 to Absolute Maximum Ratings table	5
<u>•</u>	Added output current row with upper limit of 400 µA to Absolute Maximum Ratings table	. 5
CI	nanges from Revision H (May 2016) to Revision I	ge
•	Changed Thermal Information data for INA168-Q1 DBV device	6
CI	nanges from Revision G (January 2014) to Revision H	ge
•	已更改 <i>应用</i> 要点	1
•	已添加器件信息,ESD 额定值,建议运行条件,热性能信息表,特性 描述,应用和实施,电源相关建议,布局,器件和文档支持以及机械、封装和可订购信息部分	. 1
•	已添加新的汽车合规 特性 要点并删除了原有要点	
•	为所有图片添加了引脚名称并删除了所有引脚编号	
•	Deleted Ordering Information table; information available in the Package Option Addendum at the end of this data sheet	
•	Added missing minus sign to V _{IN} pin in pin configuration figures	4
•	Deleted thermal resistance from Absolute Maximum Ratings table; see new Thermal Information table	
•	Changed R _{0JA} value for both packages	6
•	Changed V _S to V+ throughout data sheet for consistency	6
•	Changed R _{OUT} in <i>Electrical Characteristics</i> table to R _L for consistency	6
•	Changed V _{IN} to V _{SENSE} in Figure 4	7
•	Deleted V _S symbol from text regarding voltage drop in <i>Operation</i> section	10
•	Changed 10 μA to 100 μA in <i>Operation</i> section (typo)	10
•	Changed Figure 9; removed incorrect pin numbers, and moved embedded table to outside of figure	11



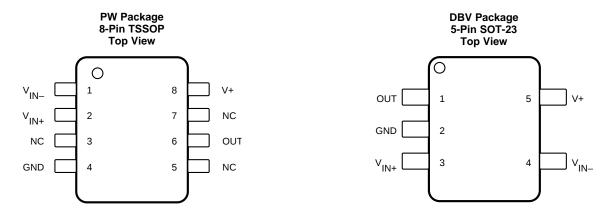


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Changed Figure 10	
Changed Figure 15	
Changes from Revision F (November 2013) to Revision G	Page
• 已将通篇文档中多处出现的部件编号 IN168-Q1 更改为 INA168-Q1	l 1
Changes from Revision E (September 2012) to Revision F	Page
Corrected Y-axis label of QUIESCENT CURRENT versus POWE	R-SUPPLY VOLTAGE graph7



5 Pin Configuration and Functions



Pin Functions

PIN					
NAME	INA138-Q1, INA168-Q1	INA168-Q1	I/O	DESCRIPTION	
	TSSOP-8	SOT-23-5			
GND	4	2	_	Ground	
NC	3, 5, 7	_	_	No internal connection	
OUT	6	1	0	Output current	
V+	8	5	I	Power-supply voltage	
V_{IN-}	1	4	I	Negative input voltage	
V_{IN+}	2	3	I	Positive input voltage	



Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

				MIN	MAX	UNIT
	Cumply V	0 1 1		-0.3	60	
	Supply, V+		INA168-Q1	-0.3	75	
Voltage	Analog inputs, V _{IN+} , V _{IN-}	Common-mode	INA138-Q1	-0.3	60	V
		Common-mode	INA168-Q1	-0.3	75	V
	Differential, V _{SE}		$(V_{IN+} - V_{IN-})^{(2)}$	-40	40	
	Analog output, OUT				40	
Current	Output current, I _{OUT} (2)	utput current, I _{OUT} ⁽²⁾			400	μA
	Operating, T _A			– 55	150	
Temperature	Junction, T _J				150	°C
	Storage, T _{stg}			-65	150	

Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

Use the following equation to make sure that the maximum value of I_{OUT} in a given application is less than 400 µA:

$$I_{OUT,MAX} = MIN \left(\frac{V_{SENSE,MAX}}{5 \text{ k}\Omega}, \frac{V_{IN+,MAX}}{10 \text{ k}\Omega + R_{LOAD}}, \frac{V+_{MAX}}{5 \text{ k}\Omega + R_{LOAD}} \right)$$

- I_{OUT,MAX} is the estimated maximum value of I_{OUT}
 V_{SENSE,MAX} is the maximum possible value of the differential input voltage in the application
- \bullet V_{IN+,MAX} is the maximum possible value of V_{IN+} in the application
- V+MAX is the maximum possible value of V+ in the application
- \bullet R_{LOAD} is the value of the load resistor in $k\Omega$

6.2 ESD Ratings

			VALUE	UNIT
V Electronic de disente	Clastroototic diacharas	Human-body model (HBM), per AEC Q100-002 ⁽¹⁾	±2000	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per AEC Q100-011	±1000	V

⁽¹⁾ AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT	
Cumply voltage V	INA138-Q1	2.7	5	36	V	
Supply voltage, V+	INA168-Q1	2.7	5	60	V	
Common-mode voltage	INA138-Q1	2.7	12	36		
	INA168-Q1	2.7	12	60	V	
Operating temperature, T _A		-40	25	125	°C	



6.4 Thermal Information

——————————————————————————————————————		INA138-Q1, INA168-Q1	INA168-Q1	
	THERMAL METRIC ⁽¹⁾	PW (TSSOP)	DBV (SOT-23)	UNIT
		8 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	179.1	168.3	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	62.6	73.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	107.7	28.1	°C/W
ΨЈТ	Junction-to-top characterization parameter	7.0	2.5	°C/W
ΨЈВ	Junction-to-board characterization parameter	106.0	27.6	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.5 Electrical Characteristics

at $T_A = -40$ °C to +125°C, V+ = 5 V, $V_{IN+} = 12$ V, and $R_L = 125$ k Ω (unless otherwise noted)

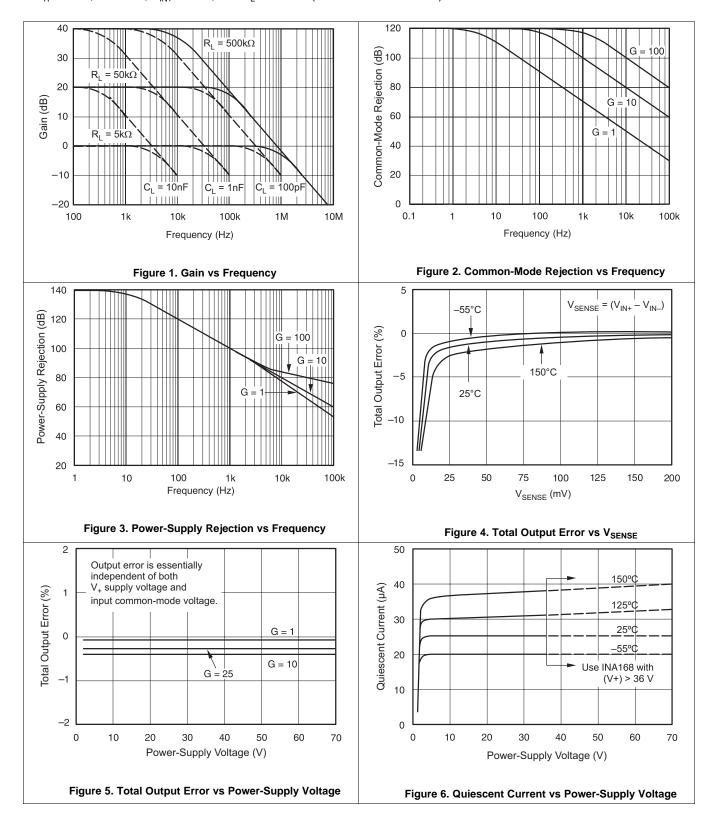
DADAMETED	TEST COMPITIONS		INA138-Q1	1	INA168-Q1				
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNIT	
INPUT									
Full-scale sense voltage	V _{SENSE} = V _{IN+} - V _{IN-}		100	500		100	500	mV	
Common mode rejection	V _{IN+} = 2.7 V to 36 V, V _{SENSE} = 50 mV	100	120						
Common-mode rejection	V _{IN+} = 2.7 V to 60 V, V _{SENSE} = 50 mV				100	120		dB	
Offset voltage ⁽¹⁾			±0.2	±2		±0.2	±2	mV	
Offset voltage vs temperature			1			1		μV/°C	
Offset voltage vs power supply	V+ = 2.7 V to 36 V, V _{SENSE} = 50 mV		0.1	10				1/0/	
(V+)	V+ = 2.7 V to 60 V, V _{SENSE} = 50 mV					0.1	10	μV/V	
Input bias current	V _{IN+} = V _{IN-} = 12 V			10			10	μА	
OUTPUT									
Transconductance	V _{SENSE} = 10 mV to 150 mV	194		206	194		206	μA/V	
Transconductance versus temperature	V _{SENSE} = 100 mV		10			10		nA/°C	
Nonlinearity error	V _{SENSE} = 10 mV to 150 mV		±0.01%	±0.2 %		±0.01%	±0.2 %		
Total output error	V _{SENSE} = 100 mV		±0.5%	±3.2%		±0.5%	±3.2%		
Output impedance			1 5			1 5		GΩ pF	
Voltage output swing to power supply (V+)			(V+) - 0.8	(V+) - 1.2		(V+) - 0.8	(V+) - 1.2	٧	
Voltage output swing to common mode, V _{CM}			V _{CM} - 0.5	V _{CM} - 1.2		V _{CM} - 0.5	V _{CM} – 1.2	٧	
FREQUENCY RESPONSE				*					
December de de la constante	$R_L = 5 \text{ k}\Omega$		800			800		1.11=	
Bandwidth	$R_L = 125 \text{ k}\Omega$		32			32		kHz	
C-His (0.40/)	5-V step, R_L = 5 kΩ		1.8			1.8		_	
Settling time (0.1%)	5-V step, R_L = 125 kΩ		30			30		μS	
NOISE									
Output-current noise density	T _A = 25°C		9			9		pA/√ Hz	
Total output-current noise	BW = 100 kHz		3			3		nA RMS	
POWER SUPPLY	, <u> </u>			"					
Quiescent current	V _{SENSE} = 0 V, I _O = 0 mA		25	60		25	60	μΑ	
	1								

⁽¹⁾ Defined as the amount of input voltage, V_{SENSE} , to drive the output to zero.



6.6 Typical Characteristics

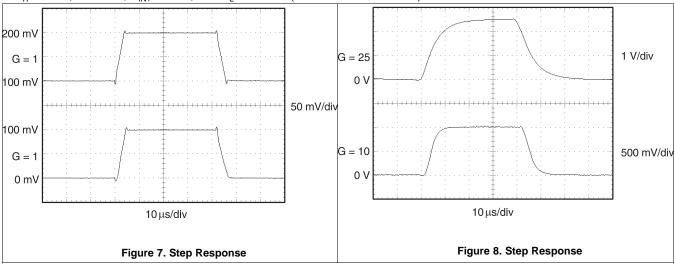
at T_A = 25°C, V+ = 5 V, V_{IN+} = 12 V, and R_L = 125 k Ω (unless otherwise noted)





Typical Characteristics (continued)

at T_A = 25°C, V+ = 5 V, V_{IN+} = 12 V, and R_L = 125 k Ω (unless otherwise noted)



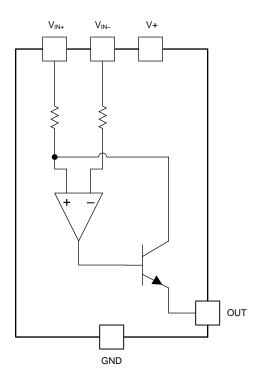


7 Detailed Description

7.1 Overview

The INA138-Q1 and INA168-Q1 devices (INA1x8-Q1) are comprised of a high-voltage, precision operational amplifier, precision thin film resistors trimmed in production to an absolute tolerance, and a low-noise output transistor. The INA1x8-Q1 are powered from a single power supply, and the input voltages can exceed the power supply voltage. The INA1x8-Q1 are ideal for measuring small differential voltages, such as those generated across a shunt resistor, in the presence of large common-mode voltages. The *Functional Block Diagram* shows the functional components within both the INA138-Q1 and INA168-Q1 devices.

7.2 Functional Block Diagram





7.3 Feature Description

7.3.1 Output Voltage Range

The output of the INA1x8-Q1 is a current that is converted to a voltage by the load resistor, R_L . The output current remains accurate within the compliance voltage range of the output circuitry. The shunt voltage and the input common-mode and power-supply voltages limit the maximum possible output swing. The maximum output voltage ($V_{out\ max}$) compliance is limited by either Equation 1 or Equation 2, whichever is lower:

$$V_{\text{out max}} = (V+) - 0.7 \ V - (V_{|N+} - V_{|N-}) \tag{1}$$

or

$$V_{\text{out max}} = V_{\text{IN}-} - 0.5 \text{ V}$$
 (2)

7.3.2 Bandwidth

Measurement bandwidth is affected by the value of the load resistor, R_L . High gain produced by high values of R_L yields a narrower measurement bandwidth (see the *Typical Characteristics* section). For the widest possible bandwidth, keep the capacitive load on the output to a minimum. Reduction in bandwidth due to capacitive load is shown in the *Typical Characteristics* section.

If bandwidth limiting (filtering) is desired, add a capacitor to the output (see Figure 12). This capacitor does not cause instability.

7.4 Device Functional Modes

For proper operation, the INA1x8-Q1 must operate within the specified limits. Operating either device outside of their specified power-supply voltage range, or their specified common-mode range, results in unexpected behavior, and is not recommended. Additionally, operating the output beyond the specified limits with respect to power-supply voltage and input common-mode voltage also produces unexpected results. See the *Electrical Characteristics* section for the device specifications.

8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

8.1.1 Operation

Figure 9 illustrates the basic circuit diagram for both the INA138-Q1 and INA168-Q1. Load current I_S is drawn from supply V_P through shunt resistor R_S . The voltage drop in the shunt resistor is forced across R_{G1} by the internal op amp, causing current to flow into the collector of Q1. External resistor R_L converts the output current, I_O , to a voltage, V_{OUT} , at the OUT pin. The transfer function for the INA1x8-Q1 is shown in Equation 3:

$$I_O = g_m \left(V_{IN+} - V_{IN-} \right)$$

where

•
$$g_m = 200 \mu A/V$$
 (3)

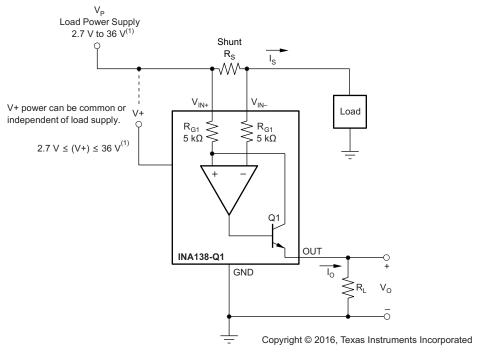
In the circuit of Figure 9, the input voltage, $(V_{IN+} - V_{IN-})$, is equal to $I_S \times R_S$. The output voltage, V_{OUT} , is equal to $I_O \times R_L$. The transconductance, g_m , of the INA1x8-Q1 is 200 μ A/V. The complete transfer function for the current measurement amplifier in this application is shown in Equation 4:

$$V_{OUT} = (I_S) (R_S) (200 \,\mu\text{A/V}) (R_L) \tag{4}$$

The maximum differential input voltage for accurate measurements is 0.5 V, producing a 100- μ A output current. A differential input voltage of up to 2 V does not cause damage. Differential measurements (V_{IN+} and V_{IN-} pins) must be unipolar, with a more-positive voltage applied to the V_{IN+} pin. If a more-negative voltage is applied to the V_{IN+} pin, I_O goes to zero, but no damage occurs.



Application Information (continued)



(1) Maximum V_P and V+ voltage is 60 V with INA168-Q1.

Figure 9. Basic Circuit Connections

Table 1. Voltage Gains and Corresponding Load-Resistor Values

VOLTAGE GAIN	EXACT R _L (kΩ)	NEAREST 1% R _L ($k\Omega$)
1	5	4.99
2	10	10
5	25	24.9
10	50	49.9
20	100	100
50	250	249
100	500	499



8.2 Typical Applications

The INA1x8-Q1 are designed for current-shunt measurement circuits (see Figure 9) but its basic function is useful in a wide range of circuitry. With a little creativity, many unforeseen uses can be found in measurement and level-shifting circuits. A few ideas are illustrated in the following subsections.

8.2.1 Buffering Output to Drive an ADC

Digitize the output of the INA138-Q1 or INA168-Q1 devices using a 1-MSPS analog-to-digital converter (ADC).

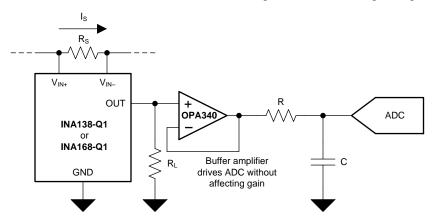


Figure 10. Buffering Output to Drive an ADC

8.2.1.1 Design Requirements

For this design example, use the input parameters shown in Table 2.

 DESIGN PARAMETER
 EXAMPLE VALUE

 Supply voltage, V+
 5 V

 Common-mode voltage, V_{CM}
 INA138-Q1: 2.7 V to 36 V

 INA168-Q1: 2.7 V to 60 V
 INA168-Q1: 2.7 V to 60 V

 Full-scale shunt voltage, V_{SENSE}
 50 mV to 100 mV

 Load resistor, R_I
 5 kΩ to 500 kΩ

Table 2. Design Parameters

8.2.1.2 Detailed Design Procedure

8.2.1.2.1 Selecting R_s and R₁

In Figure 10, the value chosen for the shunt resistor, R_S , depends on the application and is a compromise between small-signal accuracy and maximum permissible voltage loss in the measurement line. High values of R_S provide better accuracy at lower currents by minimizing the effects of offset, while low values of R_S minimize voltage loss in the supply line. For most applications, best performance is attained with an R_S value that provides a full-scale shunt voltage range of 50 mV to 100 mV. Maximum input voltage for accurate measurements is 500 mV.

Choose an R_L that provides the desired full-scale output voltage. The output impedance of the INA1x8-Q1 OUT pin is very high, permitting the use of R_L values up to 500 k Ω with excellent accuracy. The input impedance of any additional circuitry at the output must be much higher than the value of R_L to avoid degrading accuracy.

Some ADCs have input impedances that significantly affects measurement gain. The input impedance of the ADC can be included as part of the effective R_L if the ADC input can be modeled as a resistor to ground. Alternatively, an op amp can be used to buffer the ADC input, as shown in Figure 10. The INA1x8-Q1 are current output devices, and as such, have an inherently large output impedance. The output currents from the amplifier are converted to an output voltage using the load resistor, R_L , connected from the amplifier output to ground. The ratio of the load resistor value to that of the internal resistor value determines the voltage gain of the system.



In many applications, digitizing the output of the INA1x8-Q1 is required. Digitizing is accomplished by connecting the output of the amplifier to an ADC. It is very common for an ADC to have a dynamic input impedance. If the INA1x8-Q1 output is connected directly to an ADC input, the input impedance of the ADC is effectively connected in parallel with gain setting resistor R_L . This parallel impedance combination affects the gain of the system and the impact on the gain is difficult to estimate accurately. A simple solution that eliminates the paralleling of impedances, and simplifies the gain of the circuit is to place a buffer amplifier, such as the OPA340, between the output of the INA1x8-Q1 and the input to the ADC.

Figure 10 illustrates this concept. Notice that a low-pass filter is placed between the OPA340 output and the input to the ADC. The filter capacitor is required to provide any instantaneous demand for current required by the input stage of the ADC. The filter resistor is required to isolate the OPA340 output from the filter capacitor in order to maintain circuit stability. The values for the filter components vary according to the operational amplifier used for the buffer and the particular ADC selected. More information regarding the design of the low-pass filter is found in the TI Precision Design, 16 bit 1MSPS Data Acquisition Reference Design for Single-Ended Multiplexed Applications.

Figure 11 shows the expected results when driving an ADC at 1 MSPS with and without buffering the INA1x8-Q1 output. Without the buffer, the high impedance of the INA1x8-Q1 reacts with the input capacitance and sample-and-hold capacitance of the ADC, and does not allow the sampled value to reach the correct final value before the ADC is reset, and the next conversion starts. Adding the buffer amplifier significantly reduces the output impedance driving the sample-and-hold circuitry, and allows for higher conversion rates.

8.2.1.3 Application Curve

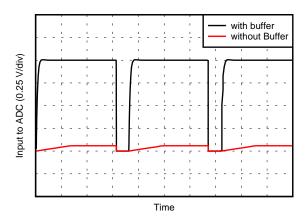


Figure 11. Driving an ADC With and Without a Buffer



8.2.2 Output Filter

Filter the output of the INA1x8-Q1 devices.

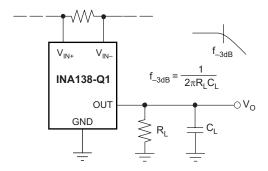


Figure 12. Output Filter

8.2.2.1 Design Requirements

For this design example, use the input parameters shown in Table 3.

 DESIGN PARAMETER
 EXAMPLE VALUE

 Supply voltage, V+
 INA138-Q1: 2.7 V to 36 V

 INA168-Q1: 2.7 V to 60 V
 INA138-Q1: 2.7 V to 36 V

 Common-mode voltage, V_{CM}
 INA168-Q1: 2.7 V to 60 V

 Full-scale shunt voltage, V_{SENSE}
 50 mV to 100 mV

 Load resistor, R_I
 5 kΩ to 500 kΩ

Table 3. Design Parameters

8.2.2.2 Detailed Design Procedure

A low-pass filter can be formed at the output of the INA1x8-Q1 simply by placing a capacitor of the desired value in parallel with the load resistor. First, determine the value of the load resistor needed to achieve the desired gain by using Table 1. Next, determine the capacitor value that results in the desired cutoff frequency according to the equation shown in Figure 12. Figure 13 shows various combinations of gain settings (determined by R_L) and filter capacitors.

8.2.2.3 Application Curve

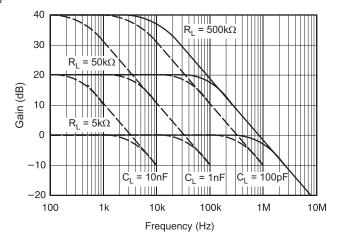


Figure 13. Gain vs Frequency



8.2.3 Offsetting the Output Voltage

For many applications using only a single power supply, the output voltage may have to be level shifted away from ground when there is no load current flowing in the shunt resistor. Level shifting the output of the INA1x8-Q1 is easily accomplished by one of two simple methods shown in Figure 14. Method (a) on the left-hand side of Figure 14 shows a simple voltage-divider method. This method is useful for applications that require the output of the INA1x8-Q1 to remain centered with respect to the power supply at zero load current through the shunt resistor. Using this method, the gain is determined by the parallel combination of R_1 and R_2 , while the output offset is determined by the voltage divider ratio of R_1 and R_2 , as shown in Figure 14(a). For applications that require a fixed value of output offset independent of the power-supply voltage, use current-source method (b) shown on the right-hand side of Figure 14. With this method, a REF200 constant current source is used to generate a constant output offset. Using this method, the gain is determined by R_L , and the offset is determined by the product of the value of the current source and R_L .

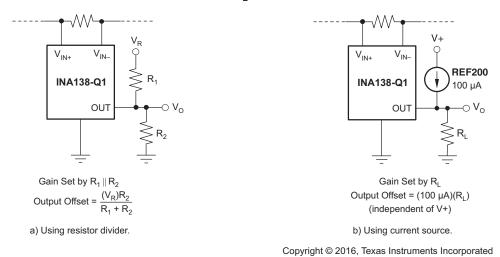


Figure 14. Offsetting the Output Voltage

8.2.4 Bipolar Current Measurement

Configure the INA1x8-Q1 as illustrated in Figure 15 for applications where bidirectional current measurement is required. Two INA1x8-Q1 devices are required; connect the inputs across the shunt resistor; see Figure 15. A comparator, such as the TLV3201, is used to detect the polarity of the load current. The magnitude of the load current is monitored across the resistor connected between ground and the connection labeled Output. In this example, the $100-k\Omega$ resistor results in a gain of 20 V/V. The $10-k\Omega$ resistors connected in series with the INA1x8-Q1 output current are used to develop a voltage across the comparator inputs. Two diodes are required to prevent current flow into the INA1x8-Q1 output because only one device at a time provides current to the Output connection of the circuit. The circuit functionality is illustrated in Figure 16.



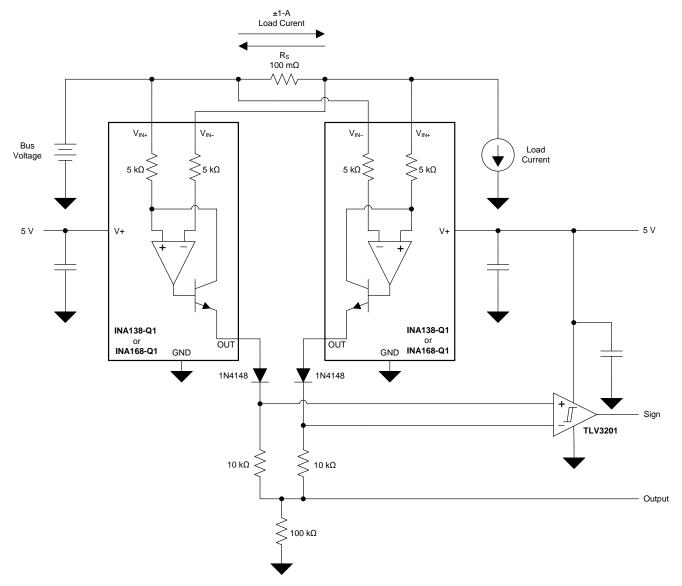


Figure 15. Bipolar Current Measurement

8.2.4.1 Application Curve

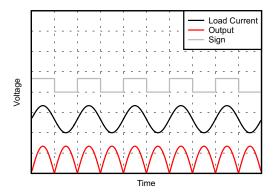


Figure 16. Bipolar Current Measurements Results (Arbitrary Scale)



8.2.5 Bipolar Current Measurement Using Differential Input of an ADC

Use the INA1x8-Q1 with an ADC such as the ADS7870 programmed for differential-mode operation; Figure 17 shows this configuration. In this configuration, the use of two INA138-Q1s or INA168-Q1s allows for bidirectional current measurement. Depending on the polarity of the current, one of the INA devices provides an output voltage, while the other INA device output is zero. In this way, the ADC reads the polarity of current directly, without the need for additional circuitry.

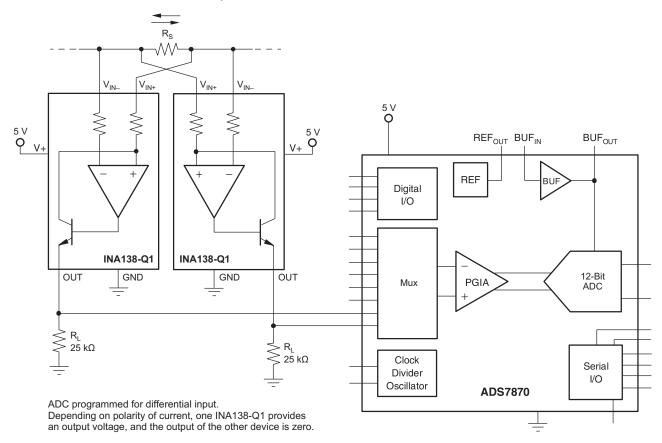


Figure 17. Bipolar Current Measurement Using Differential Input of the ADC



8.2.6 Multiplexed Measurement Using Logic Signal for Power

Measure multiple loads as shown in Figure 18. In this configuration, each INA138-Q1 or INA168-Q1 device is powered by the digital I/O from the ADS7870. Multiplexing is achieved by switching on or off each desired I/O.

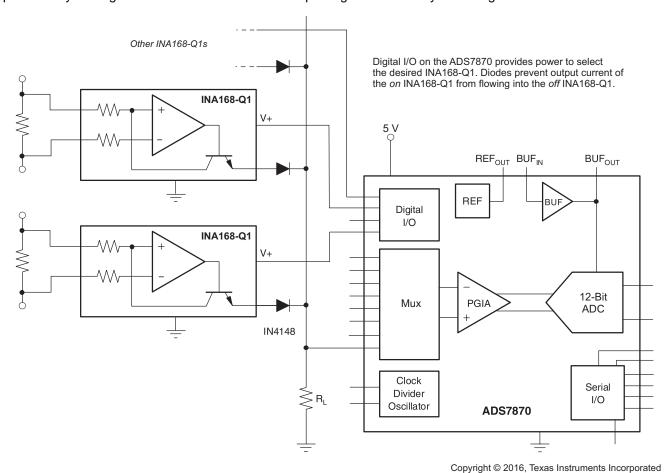


Figure 18. Multiplexed Measurement Using Logic Signal for Power



9 Power Supply Recommendations

The input circuitry of the INA1x8-Q1 can accurately measure beyond the power-supply voltage, V+. For example, the V+ power supply can be 5 V, whereas the load power-supply voltage goes up to 36 V with the INA138-Q1, or 60 V with the INA168-Q1. However, the output voltage range of the OUT pin is limited by the lesser of the two voltages (see the *Output Voltage Range* section). Place a 0.1-µF capacitor near the power-supply pin on the INA1x8-Q1. Additional capacitance may be required for applications with noisy power-supply voltages.

10 Layout

10.1 Layout Guidelines

Figure 19 shows the basic connection of the INA1x8-Q1 in the TSSOP-8 package. Connect input pins $V_{\text{IN+}}$ and $V_{\text{IN-}}$ as closely as possible to the shunt resistor to minimize any resistance in series with the shunt resistance. Output resistor R_{L} is shown connected between the OUT pin and ground. Best accuracy is achieved with the output voltage measured directly across R_{L} . Measuring directly across R_{L} is especially important in high-current systems where load current could flow in the ground connections and affect measurement accuracy.

No power-supply bypass capacitors are required for stability of the INA1x8-Q1. However, applications with noisy or high-impedance power supplies may require decoupling capacitors to reject power-supply noise. Connect bypass capacitors close to the device pins.

10.2 Layout Example

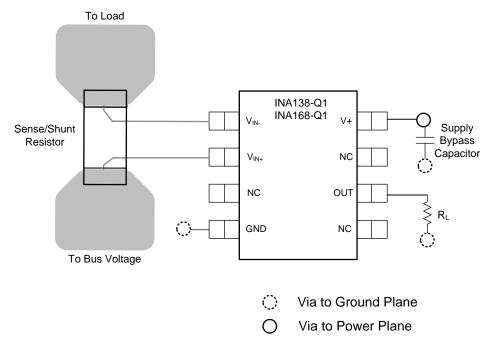


Figure 19. Typical Layout Example



11 器件和文档支持

11.1 文档支持

11.1.1 相关文档

请参阅如下相关文档:

《用于单端多路复用应用的 16 位 1MSPS 数据采集 参考设计》 TI 精密设计

11.2 相关链接

表 4 列出了快速访问链接。类别包括技术文档、支持和社区资源、工具与软件,以及立即订购快速访问。

表 4. 相关链接

器件	产品文件夹	立即订购	技术文档	工具与软件	支持和社区		
INA138-Q1	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处		
INA168-Q1	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处		

11.3 接收文档更新通知

要接收文档更新通知,请导航至 Tl.com.cn 上的器件产品文件夹。单击右上角的*通知我* 进行注册,即可每周接收产品信息更改摘要。有关更改的详细信息,请查看任何已修订文档中包含的修订历史记录。

11.4 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商"按照原样"提供。这些内容并不构成 TI 技术规范,并且不一定反映 TI 的观点:请参阅 TI 的 《使用条款》。

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设计支持 TI 参考设计支持 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

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ESD 的损坏小至导致微小的性能降级,大至整个器件故障。 精密的集成电路可能更容易受到损坏,这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

11.7 术语表

SLYZ022 — TI 术语表。

这份术语表列出并解释术语、缩写和定义。

12 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更,恕不另行通知,且不会对此文档进行修订。如需获取此数据表的浏览器版本,请查阅左侧的导航栏。



PACKAGE OPTION ADDENDUM

10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
INA138QPWRQ1	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	INA138	Samples
INA168QDBVRQ1	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LUIQ	Samples
INA168QPWRQ1	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	INA168	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

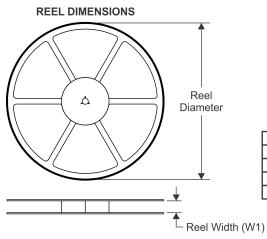
10-Dec-2020

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 6-Oct-2020

TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
INA138QPWRQ1	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
INA168QDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.15	3.1	1.55	4.0	8.0	Q3
INA168QPWRQ1	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1

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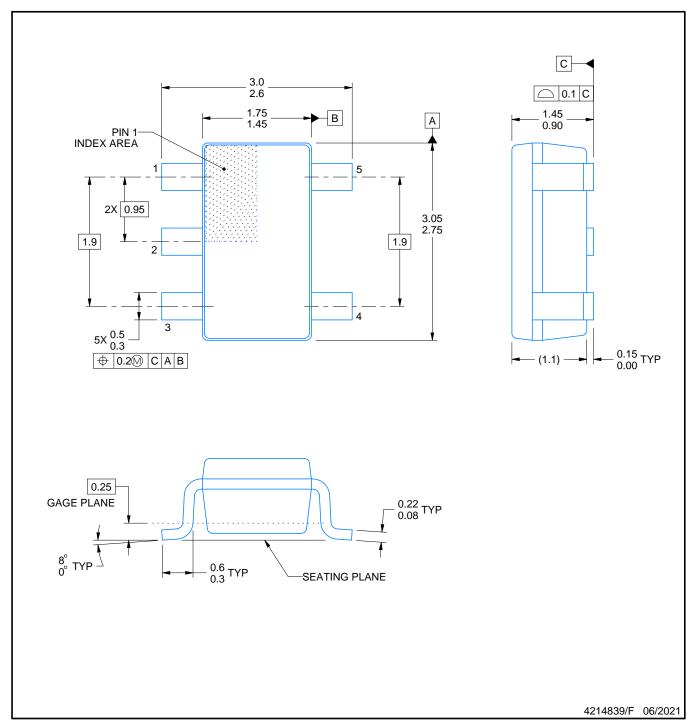


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm) Width (mm)		Height (mm)	
INA138QPWRQ1	TSSOP	PW	8	2000	367.0	367.0	35.0	
INA168QDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0	
INA168QPWRQ1	TSSOP	PW	8	2000	367.0	367.0	35.0	



SMALL OUTLINE TRANSISTOR



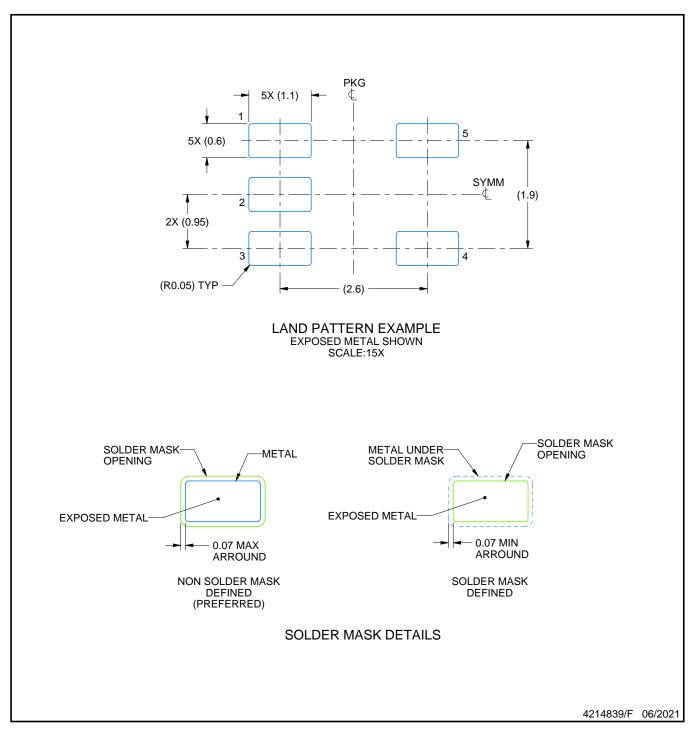
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.



SMALL OUTLINE TRANSISTOR

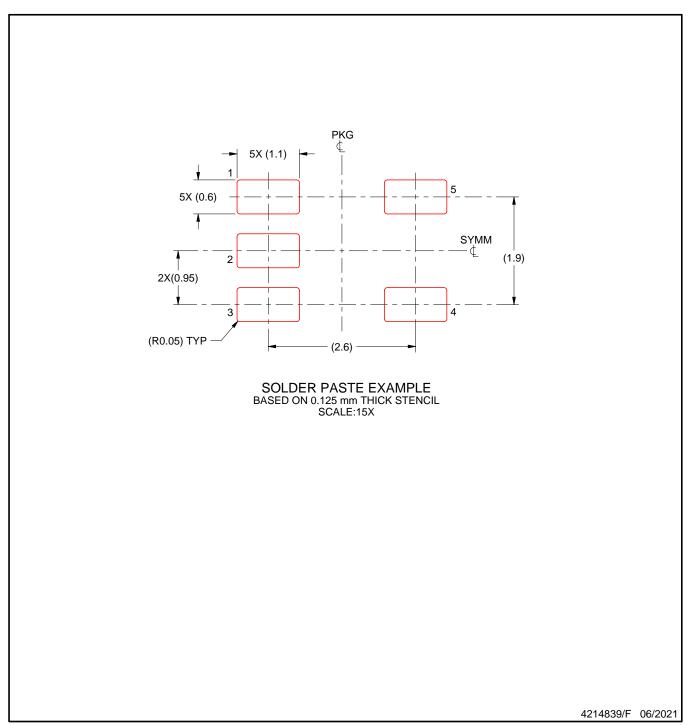


NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

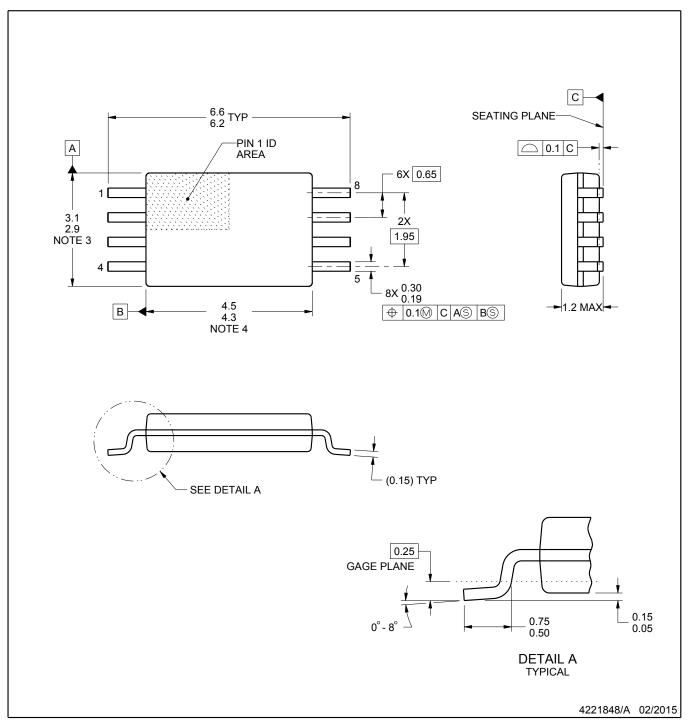


^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{8.} Board assembly site may have different recommendations for stencil design.



SMALL OUTLINE PACKAGE



NOTES:

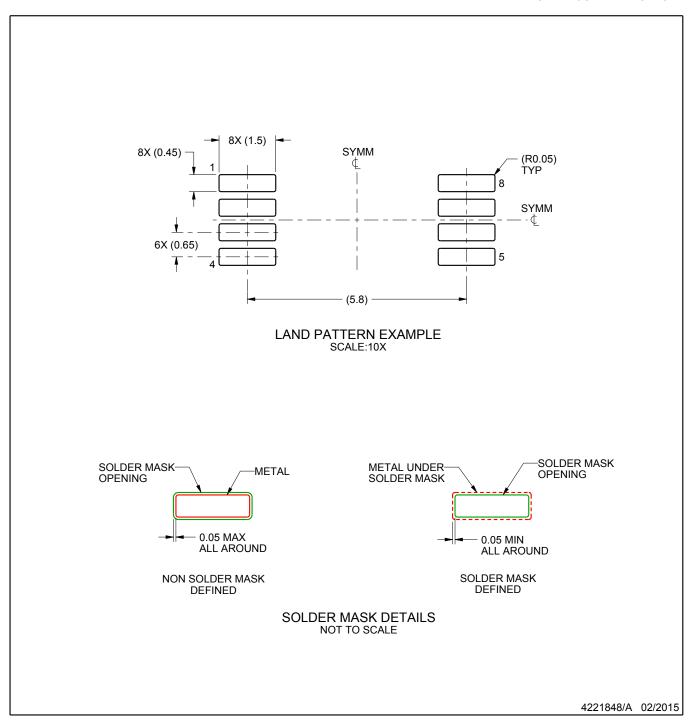
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153, variation AA.



SMALL OUTLINE PACKAGE



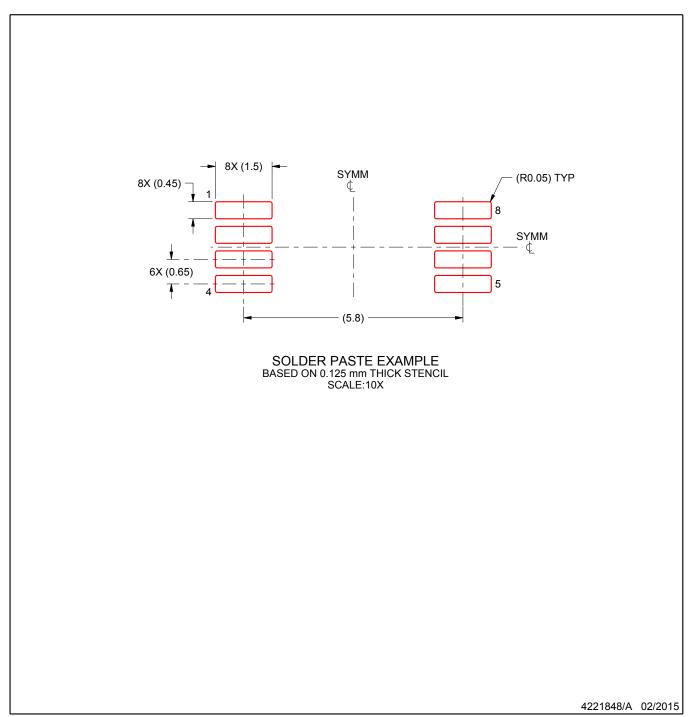
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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